

MTMC8E2A

Silicon N-channel MOS FET

For lithium-ion secondary battery protection circuit

Overview

The MTMC8E2A is the low ON resistance dual N-channel MOS FET designed for lithium-ion secondary battery protection circuit.

Features

- Low drain-source ON resistance: $R_{DS(on)}$ typ. = 15 m Ω ($V_{GS} = 4.5$ V)
- Small size surface mounting package: WMini8-F1 (2.9 mm \times 2.8 mm \times 0.8 mm)
- Drain common 2 elements
- Built-in gate resistor
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

MTMC8E2A0L Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	20	V
Gate-source surrender voltage	V_{GSS}	± 12	V
Drain current	I_D	7.0	A
Peak drain current	I_{DP}	42	A
Power dissipation	P_{D1}^{*1}	1.0	W
	$P_{D2}^{*1, *2}$	1.2	
	P_{D3}^{*3}	0.4	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1: Glass epoxy board: 25.4 mm \times 25.4 mm \times 0.8 mm

Copper foil of the drain portion should have a area of 300 mm² or more

*2: t = 10 s

*3: Stand-alone (without the board)

Package

Code

WMini8-F1

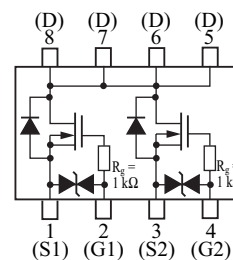
Package dimension clicks here.→

Pin Name

- | | |
|-------------|----------|
| 1: Source-1 | 5: Drain |
| 2: Gate-1 | 6: Drain |
| 3: Source-2 | 7: Drain |
| 4: Gate-2 | 8: Drain |

Marking Symbol: 4B

Internal Connection

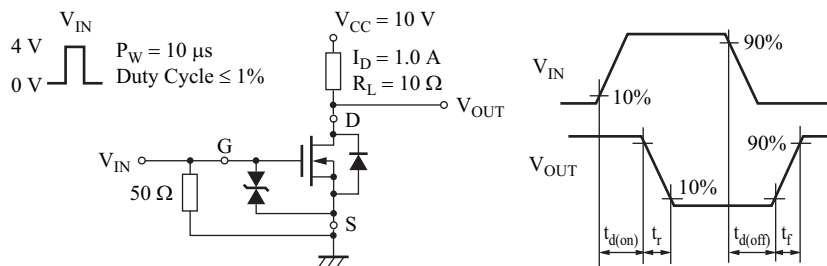


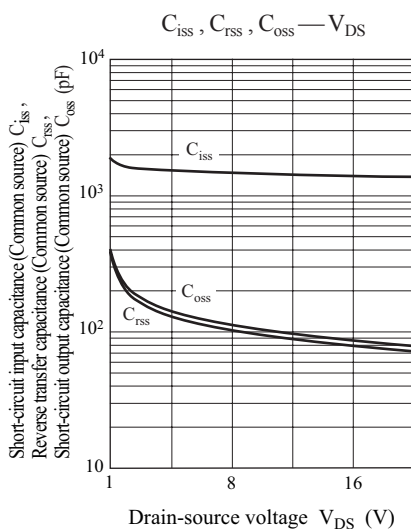
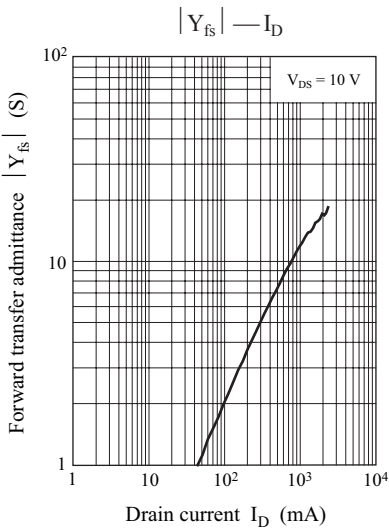
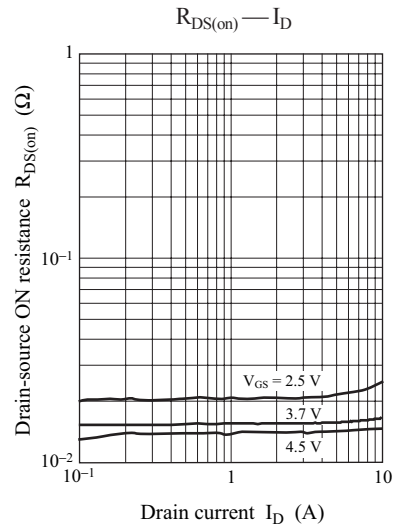
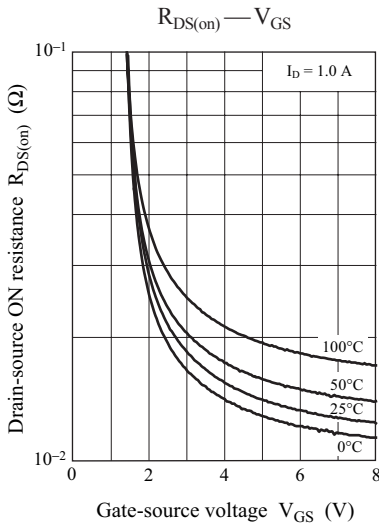
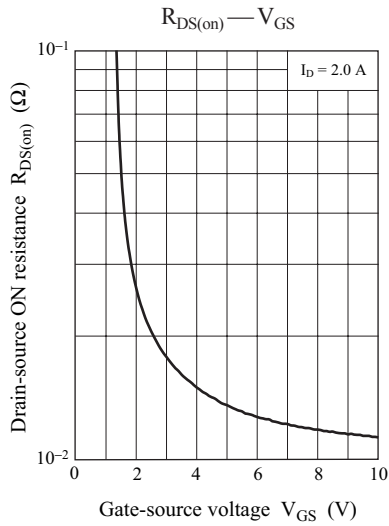
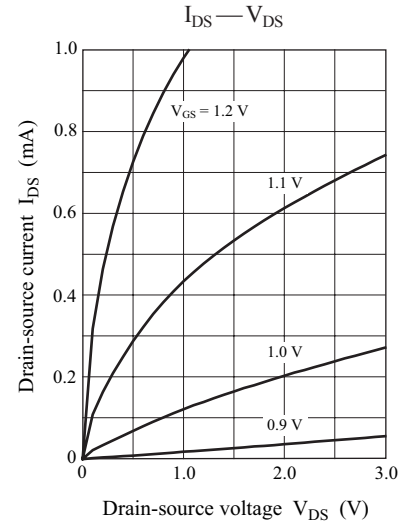
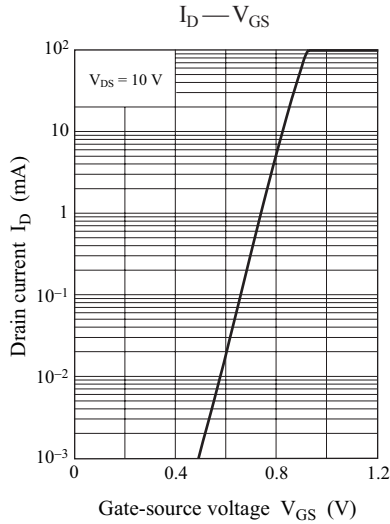
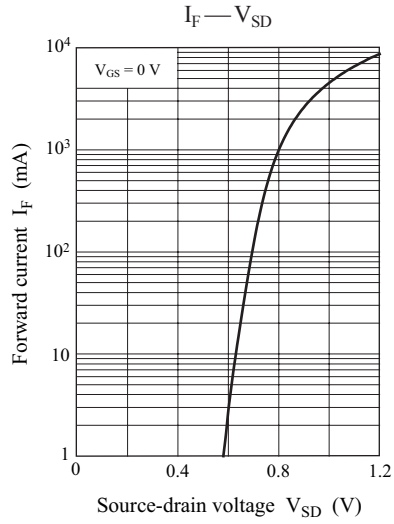
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 1.0\text{ mA}, V_{GS} = 0$	20			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0$			1.0	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 8.0\text{ V}, V_{DS} = 0$			± 10	μA
Gate threshold voltage	V_{TH}	$I_D = 1.0\text{ mA}, V_{DS} = 10\text{ V}$	0.40	0.85	1.30	V
Drain-source ON resistance 1	$R_{DS(on)1}$	$I_D = 2.0\text{ A}, V_{GS} = 4.5\text{ V}$		15	21	$\text{m}\Omega$
Drain-source ON resistance 2	$R_{DS(on)2}$	$I_D = 2.0\text{ A}, V_{GS} = 3.7\text{ V}$		18	25	$\text{m}\Omega$
Drain-source ON resistance 3	$R_{DS(on)3}$	$I_D = 1.0\text{ A}, V_{GS} = 2.5\text{ V}$		22	33	$\text{m}\Omega$
Forward transfer admittance	$ Y_{fs} $	$I_D = 1.0\text{ A}, V_{DS} = 10\text{ V}$	3.0			S
Short-circuit input capacitance (Common source)	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$		1450		pF
Short-circuit output capacitance (Common source)	C_{oss}			100		pF
Reverse transfer capacitance (Common source)	C_{rss}			90		pF
Turn-on delay time *	$t_{d(on)}$	$V_{DD} = 10\text{ V}, V_{GS} = 0\text{ V to } 4\text{ V},$ $I_D = 1.0\text{ A}$		0.33		μs
Rise time *	t_r			0.70		μs
Turn-off delay time *	$t_{d(off)}$	$V_{DD} = 10\text{ V}, V_{GS} = 4\text{ V to } 0\text{ V},$ $I_D = 1.0\text{ A}$		4.0		μs
Fall time *	t_f			2.0		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Measurement circuit





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